

# NCEP0160F

# NCE N-Channel Super Trench Power MOSFET

#### Description

The NCEP0160F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **General Features**

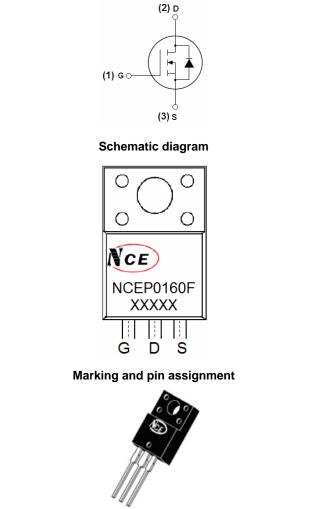
- V<sub>DS</sub> =100V,I<sub>D</sub> =60A
  - $R_{DS(ON)}$  =9.2m $\Omega$ (typical) @ V<sub>GS</sub>=10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

## Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



#### TO-220F top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0160F	NCEP0160F	TO-220F	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	60	A
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	42.4	А
Pulsed Drain Current	I <sub>DM</sub>	240	А
Maximum Power Dissipation	PD	35	W
Derating factor		0.23	W/°C
Single pulse avalanche energy <sup>(Note 5)</sup>	E <sub>AS</sub>	290	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C





### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	4.3	°C <b>/W</b>
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## **Electrical Characteristics (Tc=25**°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<b>I</b>		•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	IV,V <sub>GS</sub> =0V -		1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V -		-	±100	nA
On Characteristics (Note 3)	<b>I</b>					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , I <sub>D</sub> =250µA	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	9.2	10.8	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =30A	-	40	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	2500	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V, F=1.0MHz	-	273	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHZ	-	27	-	PF
Switching Characteristics (Note 4)	<b>I</b>		•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	13	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =50V,I <sub>D</sub> =30A	-	8.5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	_	29	-	nS
Turn-Off Fall Time	t <sub>f</sub>		_	4	-	nS
Total Gate Charge	Qg	V/ F0V/1 00A	-	37		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V,I <sub>D</sub> =30A,	_	14		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	_	8		nC
Drain-Source Diode Characteristics	· ·					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =60A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	60	Α
Reverse Recovery Time	trr	$T_J$ = 25°C, $I_F$ = $I_S$	-	58		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	149		nC

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ\!\mathrm{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

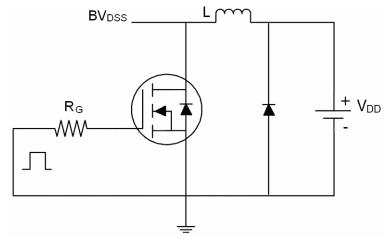


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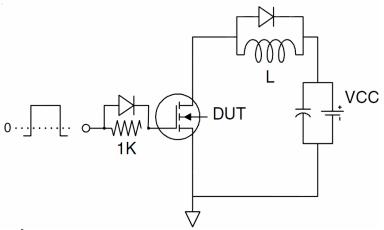
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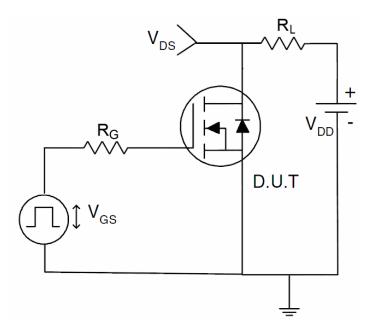
## Test Circuit 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit



## 3) Switch Time Test Circuit

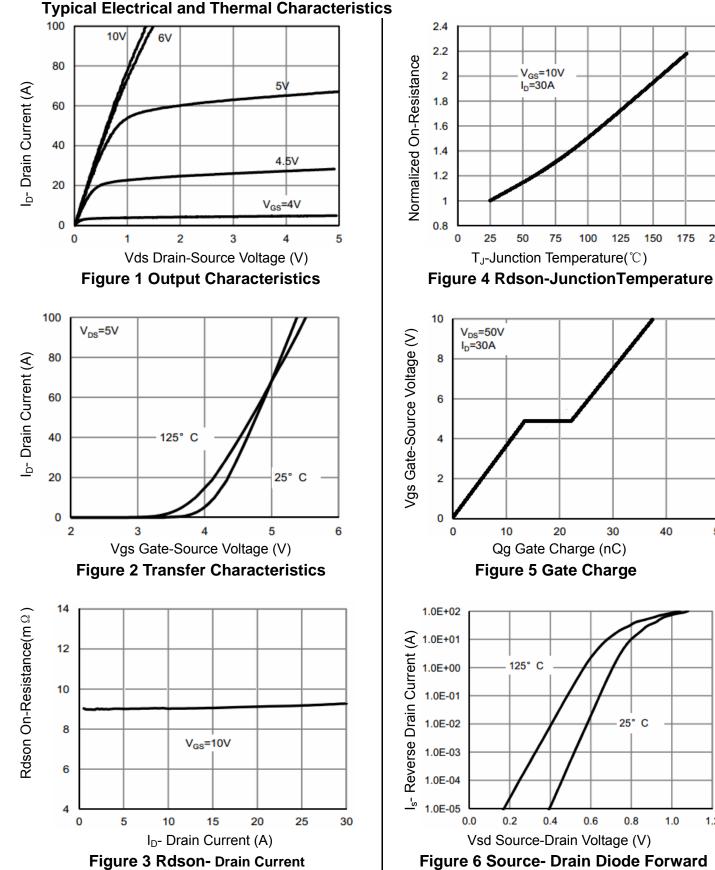


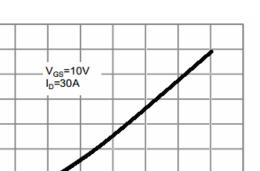


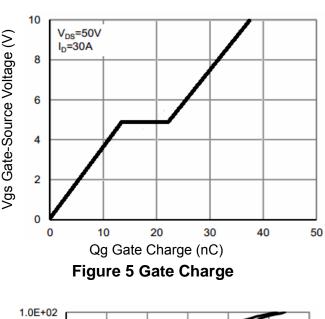
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75

100

125

150

175

200

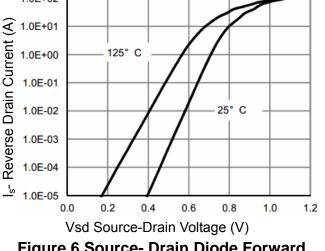
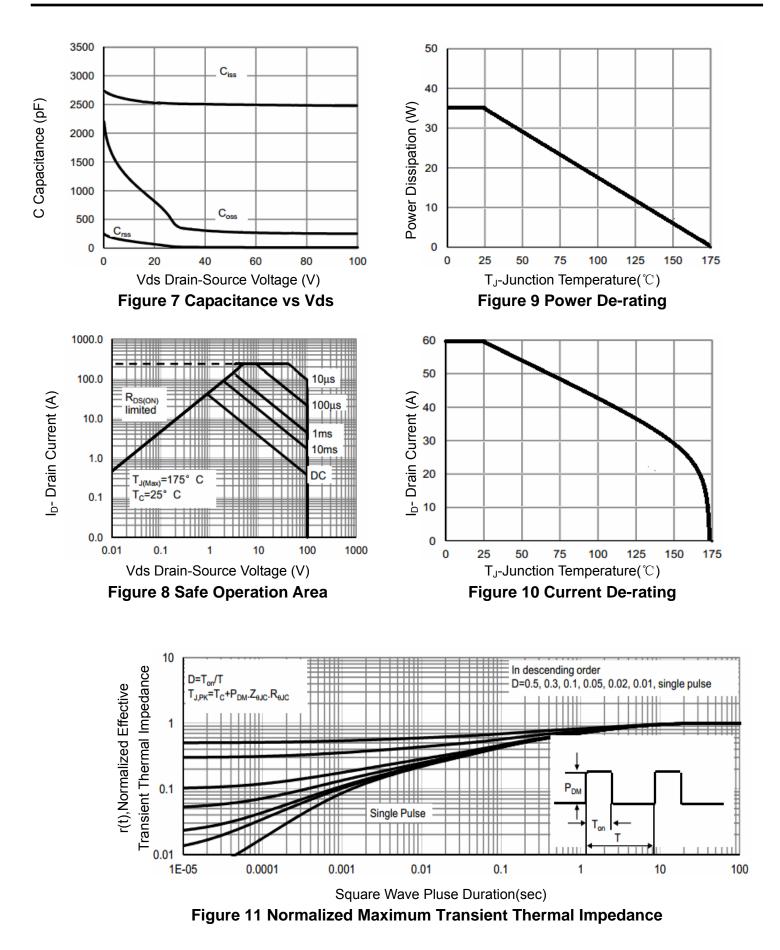


Figure 6 Source- Drain Diode Forward



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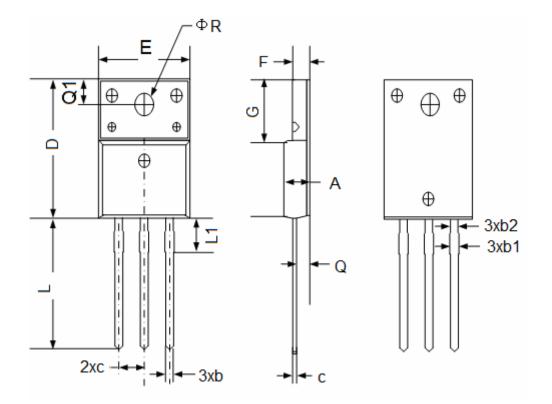


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## **TO-220F Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches				
Symbol	Min.	Max.	Min.	Max.			
A	4.50	4.83	0.18	0.19			
b	0.70	0.91	0.03	0.04			
b1	1.20	1.47	0.05	0.06			
b2	1.10	1.38	0.04	0.05			
с	0.45	0.63	0.02	0.02			
D	15.67	16.07	0.62	0.63			
е	2.54	2.54 BSC		0.10 BSC			
E	9.96	10.36	0.39	0.41			
F	2.34	2.74	0.09	0.11			
G	6.48	6.90	0.26	0.27			
L	12.68	13.30	0.50	0.52			
L1	3.13	3.50	0.12	0.14			
Q	2.56	2.93	0.10	0.12			
Q1	3.20	3.40	0.13	0.13			
ΦR	3.08	3.28	0.12	0.13			







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